

40-44GHz Down converter

GaAs Monolithic Microwave IC

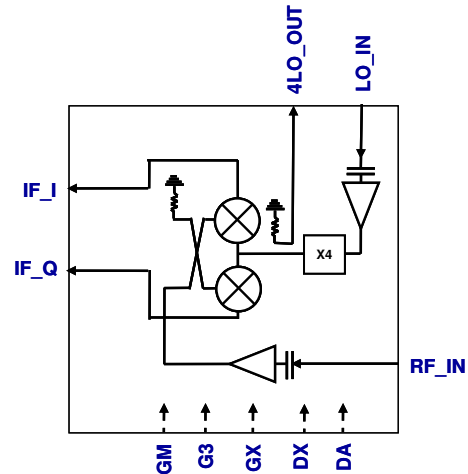
Description

The CHR2299-99F is a down converter multifunction chip, which integrates LO X4 multiplier, a balanced cold FET mixer and a RF LNA.

It is designed for a wide range of applications, from military to commercial communication systems.

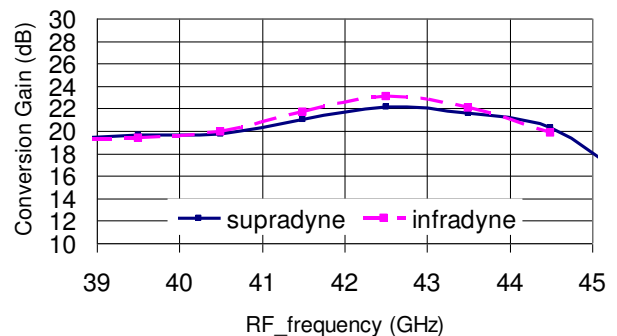
The circuit is manufactured with a power pHEMT process, 0.15 μ m gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is available in chip form.



Main Features

- 40-44GHz RF bandwidth
- 21dB conversion gain
- x4 LO frequency multiplier
- x4 LO output port
- > 12dB image rejection
- DC bias: Vd = 4V @ Id = 240mA
- Chip size 3.97x2.25x0.1mm



Main Characteristics

Tamb.= +25°C

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------|--------------------|-----|-----|------|------|
| F_RF | RF frequency range | 40 | | 44 | GHz |
| F_LO | LO frequency range | 9.5 | | 11.5 | GHz |
| F_IF | IF frequency range | DC | | 2.0 | GHz |
| Gc | Conversion gain | | 21 | | dB |

Electrical Characteristics

Tamb. = +25°C

| Symbol | Parameter | Min | Typ | Max | Unit |
|----------|---|-----|------|------|------|
| F_RF | RF frequency range | 40 | | 44 | GHz |
| F_LO | LO frequency range | 9.5 | | 11.5 | GHz |
| F_IF | IF frequency range | DC | | 2.0 | GHz |
| Gc | Conversion gain | | 21 | | dB |
| Im rej | Image rejection | | 12 | | dB |
| P_LO | LO Input power | | 0 | | dBm |
| NF | Noise figure for IF>0.1GHz | | 4.5 | | dB |
| IMD3 | Intermodulation level at Pin _{2tones} = -30dBm | | 45 | | dBc |
| RL_RF | RF Return Loss | | 6 | | dB |
| RL_LO | LO Return Loss | | 12 | | dB |
| P_4FLO | Output power at 4LO_OUT port | | -1 | | dBm |
| 4xFLO_Lk | 4xFLO leakage on RF port | | -38 | | dBm |
| DX, DA | LO multiplier, buffer and LNA biasing | | 4 | | V |
| GM | Mixer gate biasing | | -0.6 | | V |
| G3 | LO buffer gate biasing | | -0.3 | | V |
| GX | Multiplier gate biasing | | -1.2 | | V |
| IdT | Total biasing current | | 240 | | mA |

Electrostatic discharge sensitive device observe handling precautions!

These values are representative of chip on board measurements with a 90° hybrid coupler.

Absolute Maximum Ratings (1)

Tamb.= +25°C

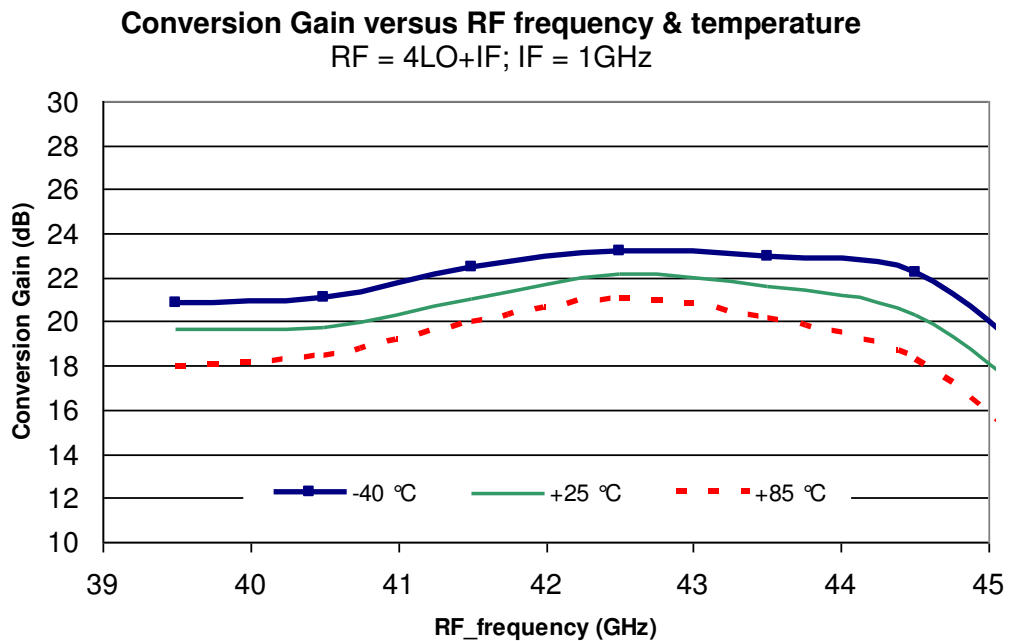
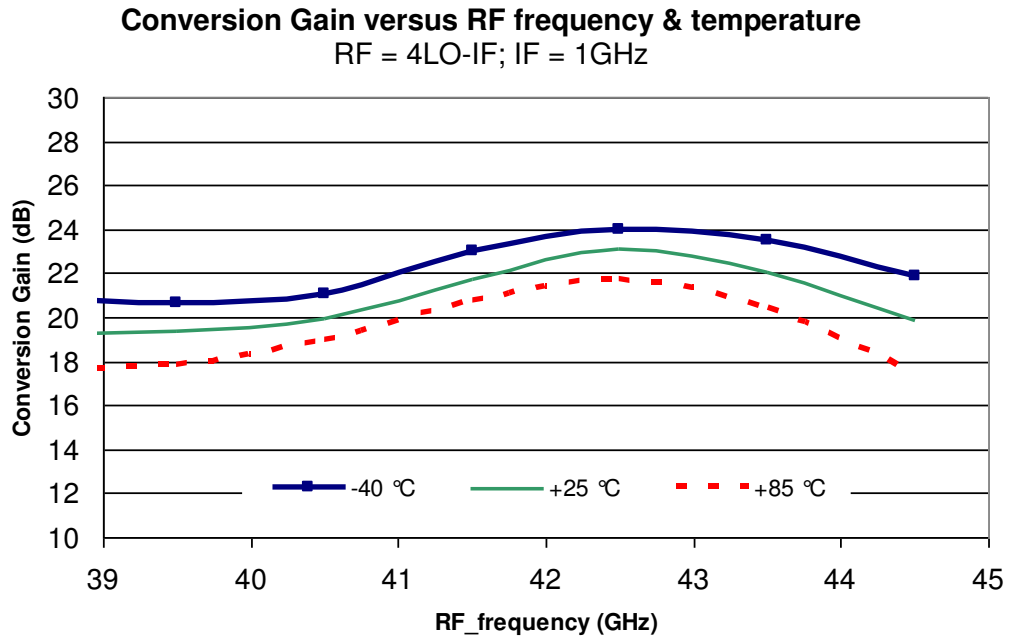
| Symbol | Parameter | Values | Unit |
|------------|--|-------------|------|
| DX, DA | LO multiplier, buffer and LNA biasing | 4.5 | V |
| IdT | Total biasing current | 300 | mA |
| GM, G3, GX | Gate bias voltage | -2; +0.6 | V |
| P_LO | Maximum peak input LO power overdrive ⁽²⁾ | 10 | dBm |
| Pin_RF | Maximum peak input RF power overdrive ⁽²⁾ | -5 | dBm |
| Tj | Junction temperature | 175 | °C |
| Ta | Operating temperature range | -40 to +85 | °C |
| Tstg | Storage temperature range | -55 to +155 | °C |
| RTh | Thermal resistance, Tback side = +85 °C, Ptotal = 0.96 W | 80 | °C/W |

⁽¹⁾ Operation of this device above anyone of these parameters may cause permanent damage

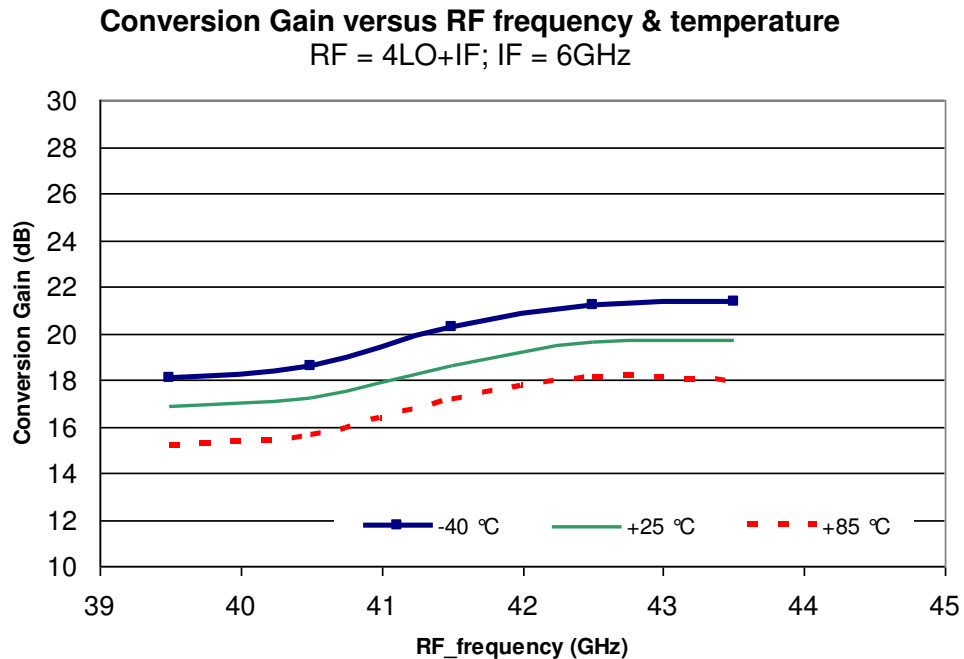
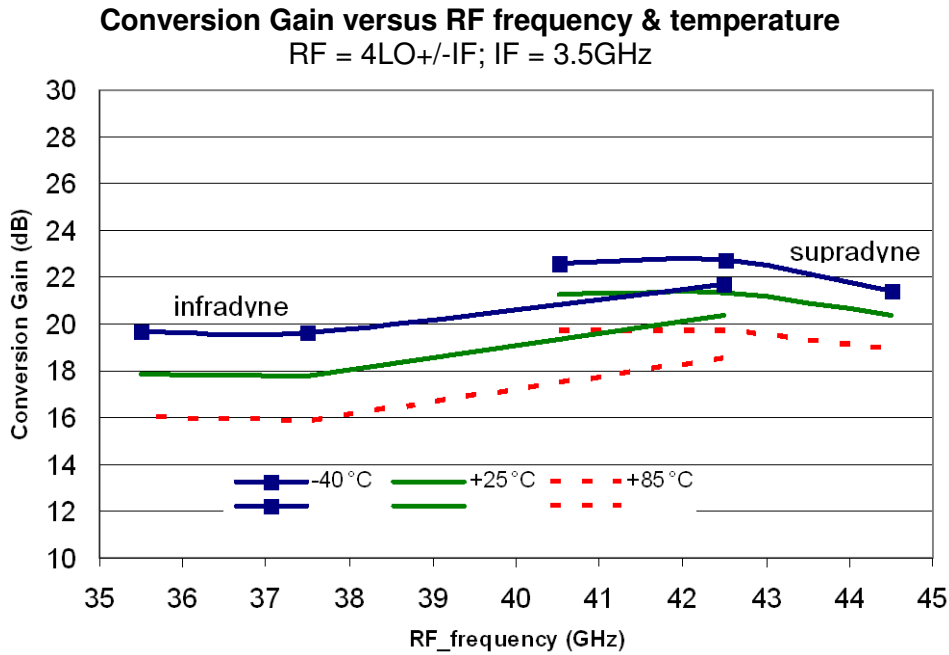
⁽²⁾ Duration < 1s

Typical chip on board Measurements in Temperature

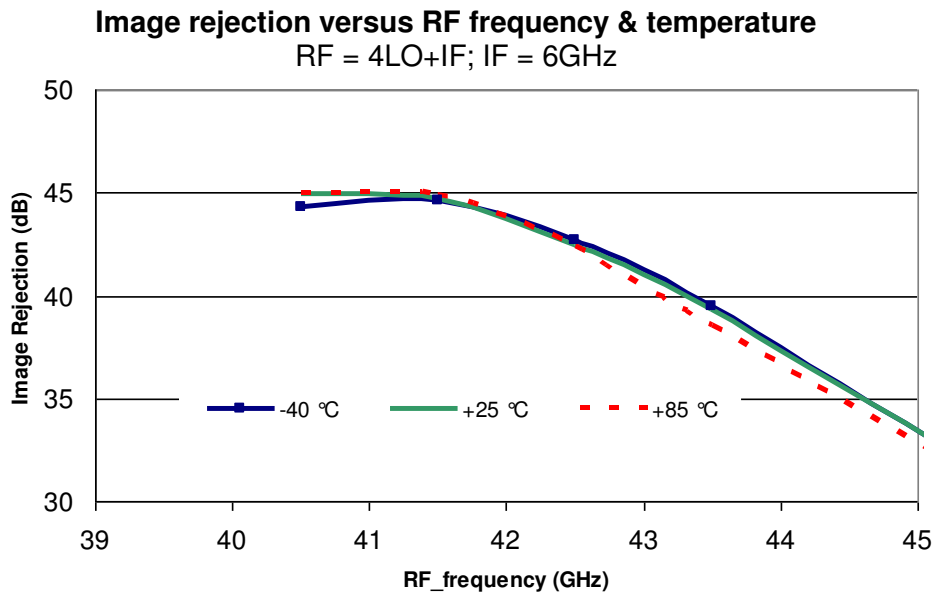
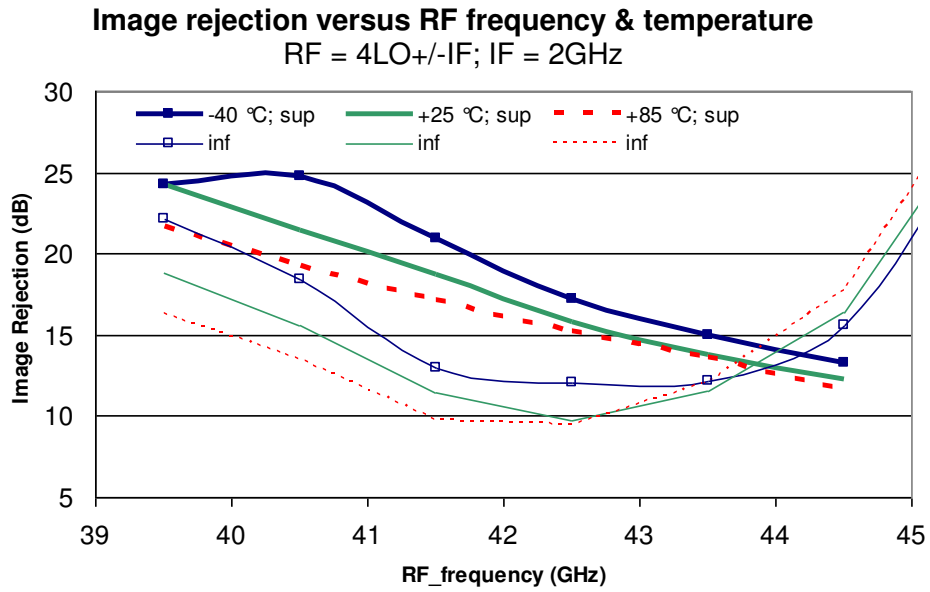
DX= DA = 4V, GM = -0.6V, G3 = -0.3V, GX = -1.2V, P_LO = 0dBm
 These values are representative of onboard measurements as defined on the section "Evaluation mother board". The losses are de-embedded.



Typical chip on board Measurements in Temperature



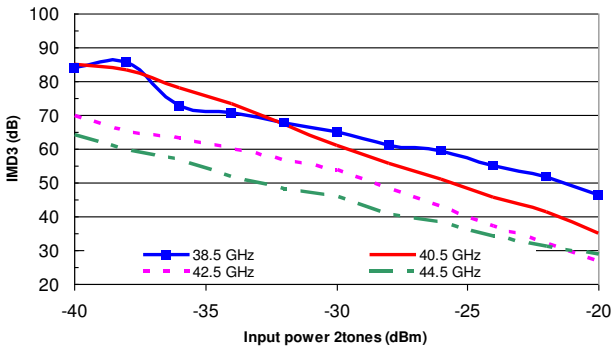
Typical chip on board Measurements in Temperature



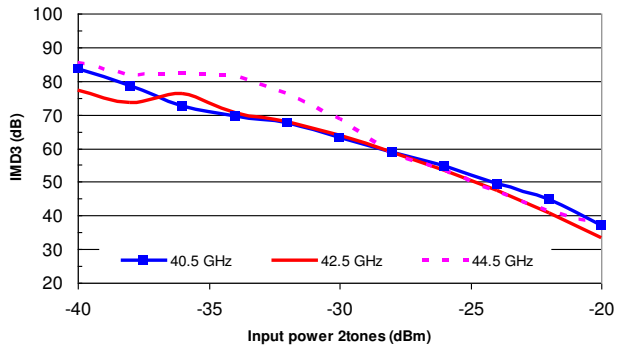
Typical chip on board Measurements

IMD3 versus RF frequency & Input power

Infradyne: IF = 2GHz

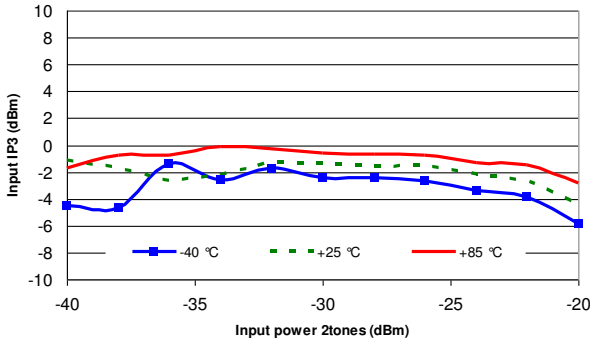


Supradyne: IF = 2GHz

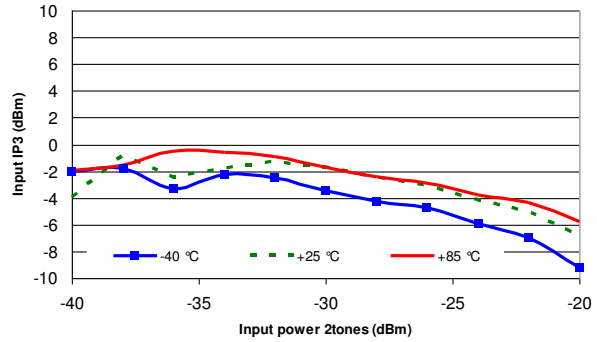


Input IP3 versus Temperature & Input power

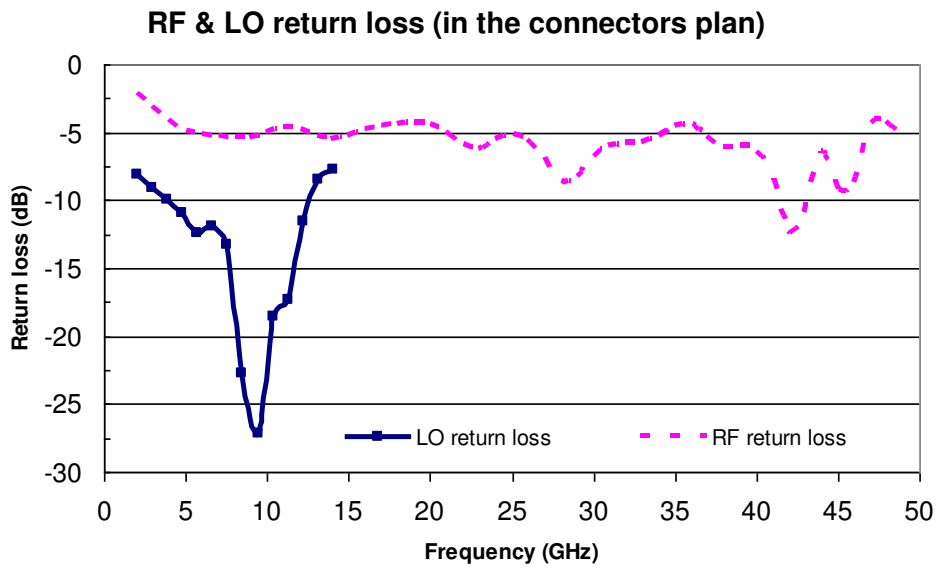
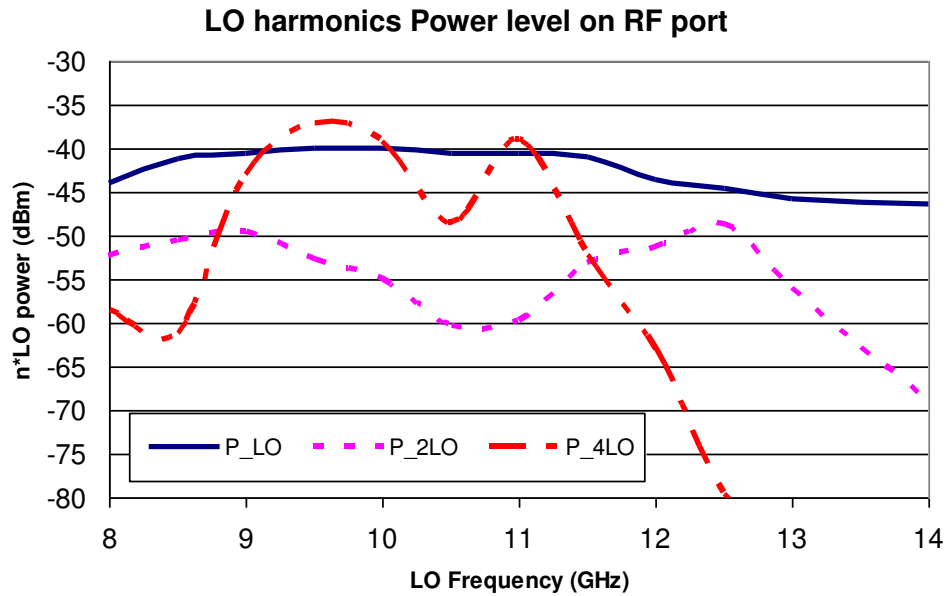
Supradyne: RF = 40.5GHz; IF = 2GHz



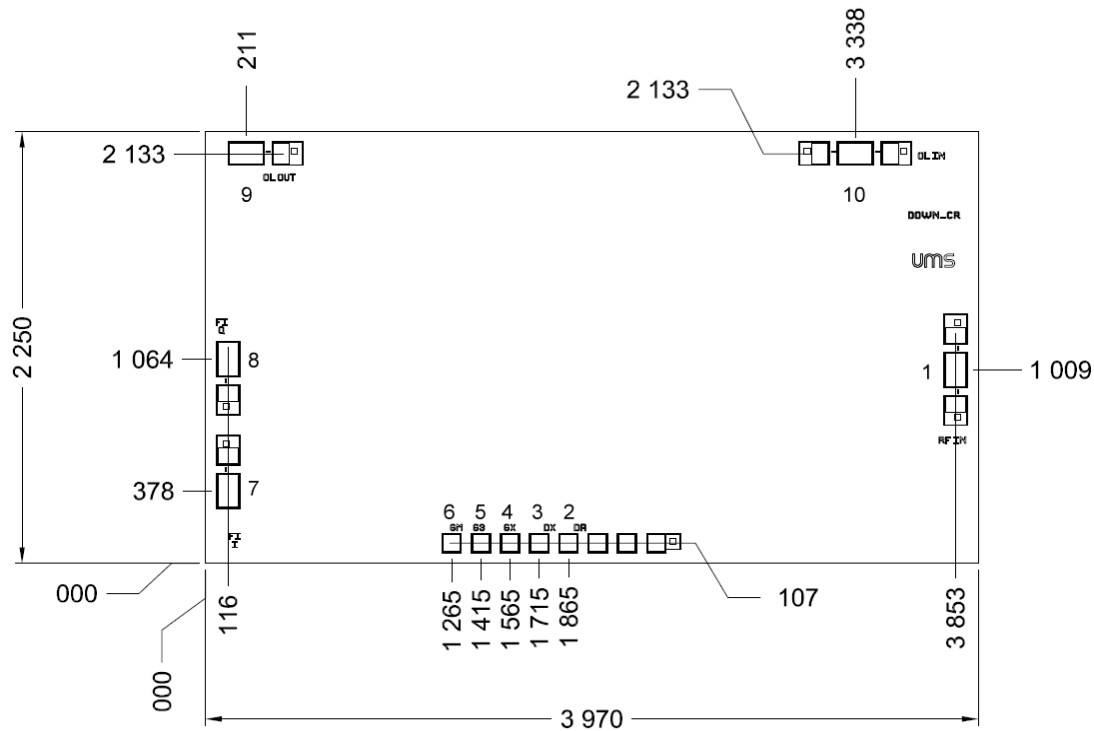
Supradyne: RF = 40.5GHz; IF = 3.5GHz



Typical chip on board Measurements



Mechanical data



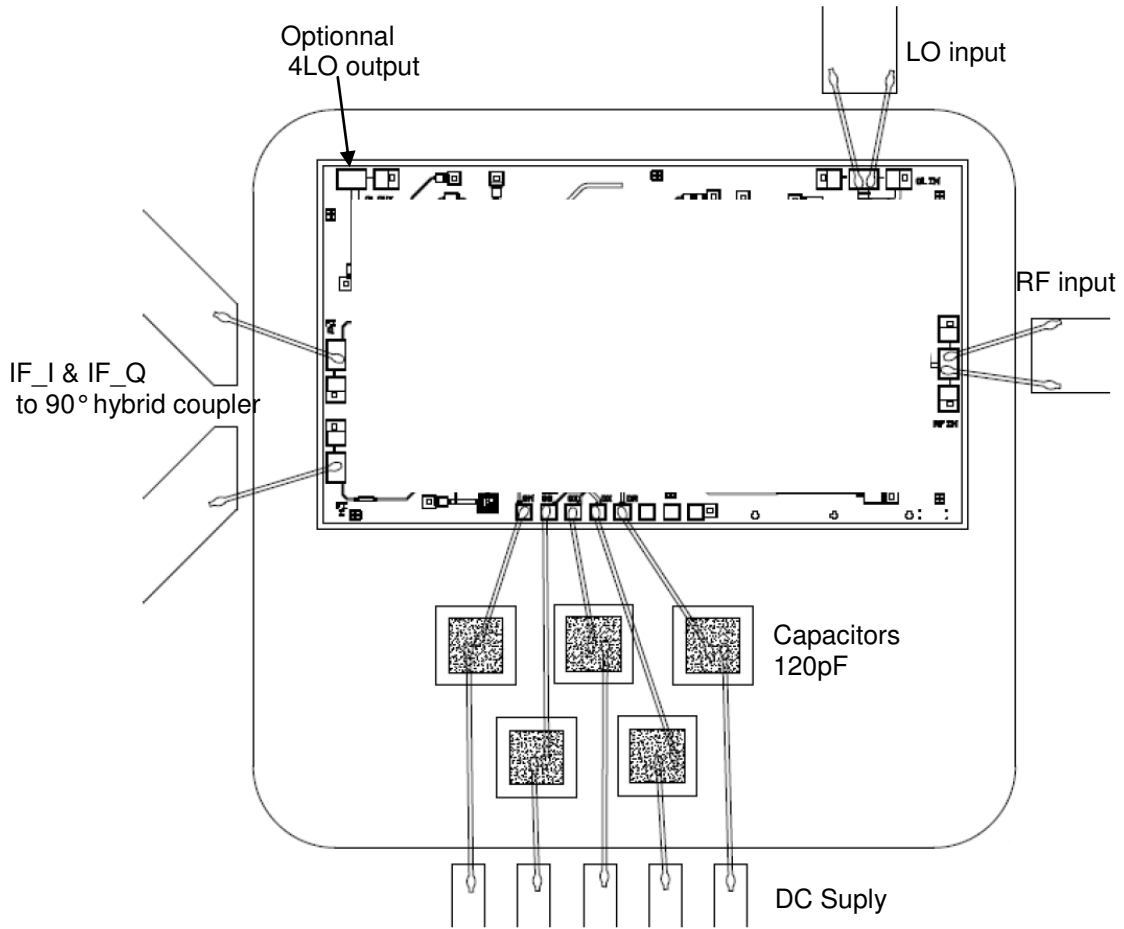
Chip thickness: 100 μm, units: μm, tol: +/- 35 μm
 DC pads = 92x92 μm, RF pads = 178x114 μm

| Pin number | Pin name | Description |
|------------|-------------|-----------------------------------|
| 1 | RF_IN | RF input |
| 2 | DA | LNA drain voltage |
| 3 | DX | Multiplier & Buffer drain voltage |
| 4 | GX | Multiplier gate voltage |
| 5 | G3 | LO buffer gate voltage |
| 6 | GM | Mixer gate voltage |
| 7, 8 | IF_I & IF_Q | IF outputs |
| 9 | 4LO_OUT | Output 4xLO frequency |
| 10 | LO_IN | LO input |

Recommended biasing

| Pin Name | Pin Number | Parameter | Nominal value |
|----------|------------|-----------------------------|---------------|
| GM | 6 | Mixer gate voltage | -0.6 V |
| G3 | 5 | LO buffer gate voltage | -0.3 V |
| GX | 4 | X4 gate voltage | -1.2 V |
| DX | 3 | X4 and buffer drain voltage | 4 V |
| DA | 2 | LNA Drain voltage | 4 V |

Chip assembly



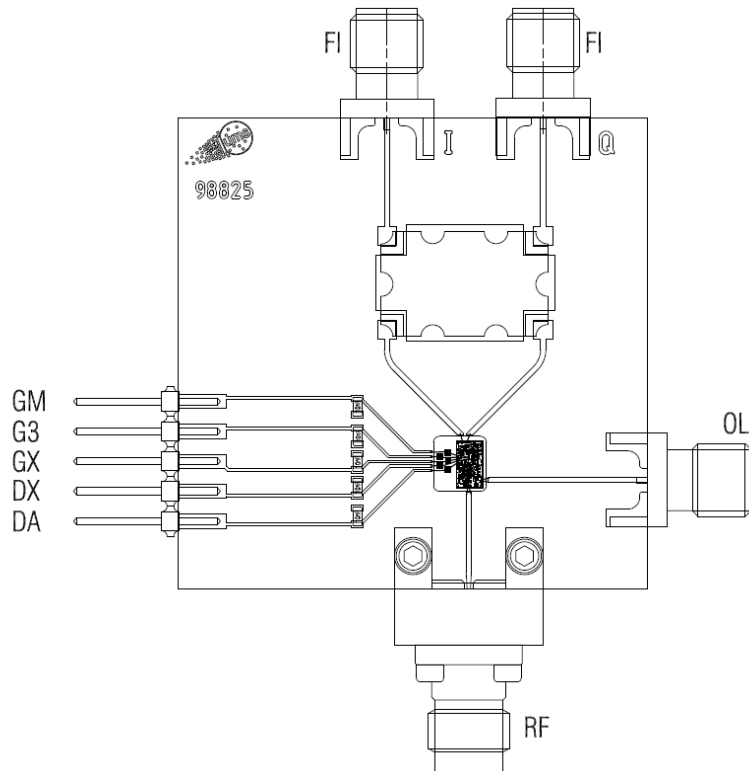
Note: Supply feed should be capacitively bypassed. 25µm diameter gold wire is recommended

Evaluation mother board

Based on typically Ro4003 / 8 mils or equivalent.

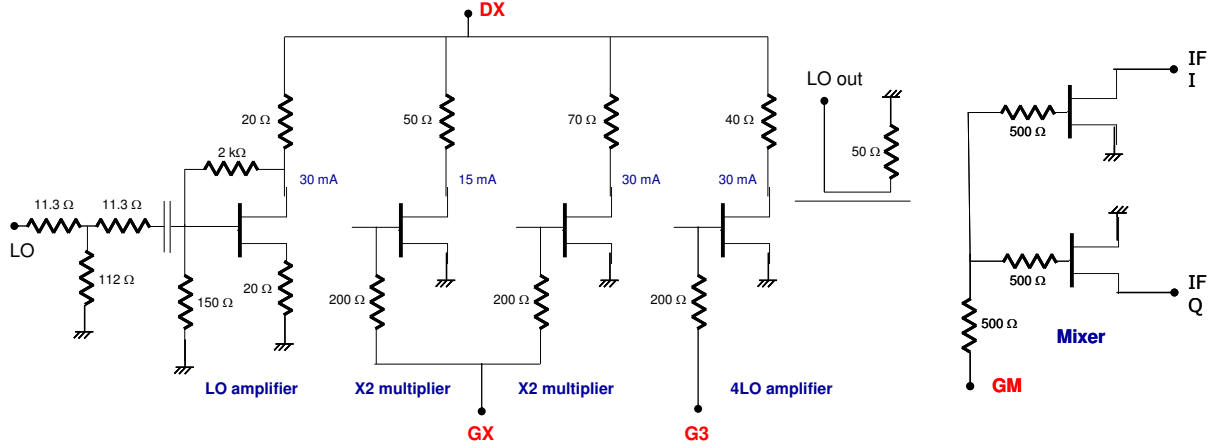
Decoupling capacitors of 10nF $\pm 10\%$ and chip 120pF $\pm 10\%$

90° hybrid coupler: 1-2GHz or 2-4GHz

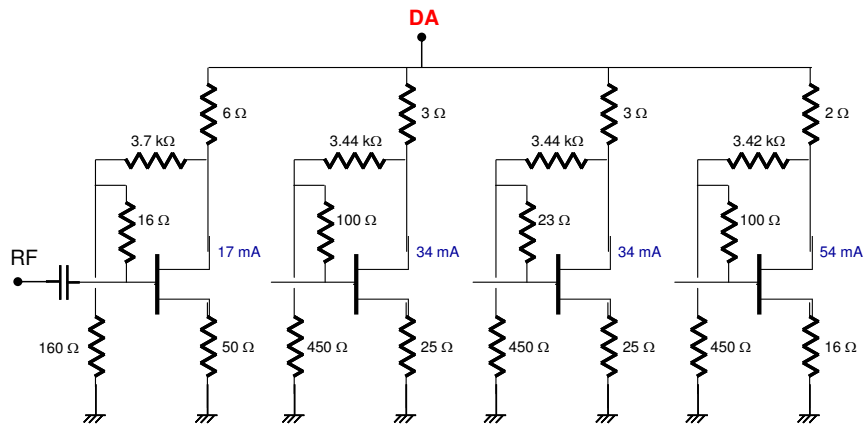


DC Schematic

LO multiplier and buffers: 4V, 105mA



LNA: 4V, 140mA



Recommended ESD management

Refer to the application note AN0020 available at <http://www.ums-gaas.com> for ESD sensitivity and handling recommendations for the UMS products.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <http://www.ums-gaas.com>.

Ordering Information

Chip form:

CHR2299-99F/00

Information furnished is believed to be accurate and reliable. However **United Monolithic Semiconductors S.A.S.** assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of **United Monolithic Semiconductors S.A.S.**. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. **United Monolithic Semiconductors S.A.S.** products are not authorised for use as critical components in life support devices or systems without express written approval from **United Monolithic Semiconductors S.A.S.**